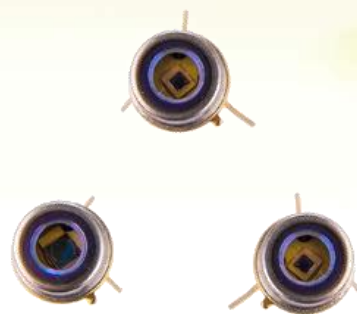


TO Series Detector

Introduction

TO Series Detector is made by, on substrate of InP with method of MOCVD to achieve InGaAs optical receiving area, then through facial spreading technique. Photosensitive area is $\Phi 300\mu\text{m}$ & $\Phi 500\mu\text{m}$, with which correct parts to be selected.



Application

- Near infra-red Optical metrology
- Optical efficiency test
- Fiber consumption test
- Spectrum test
- Micro-optical test

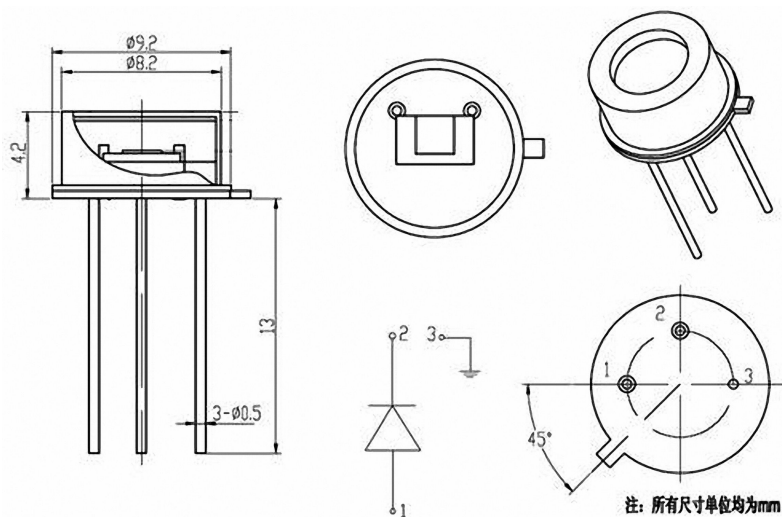
Tech Parameters (20°C)

TO Serial Optoelectronics Detector				
Parameter		$\Phi 300\mu\text{m}$	$\Phi 500\mu\text{m}$	Unit
package		TO		-
Respondent Wavelength Range		0.65 ~ 1.65		μm
Respondent (0V)	1310nm	≥ 0.75		A/W
	1550nm	≥ 0.80		A/W
Linear Range (0V)	-	-40 ~ 10		dBm
Capacitance(-5V)		≤ 12	≤ 20	pF
Dark Current(-5V)		≤ 5	≤ 10	nA



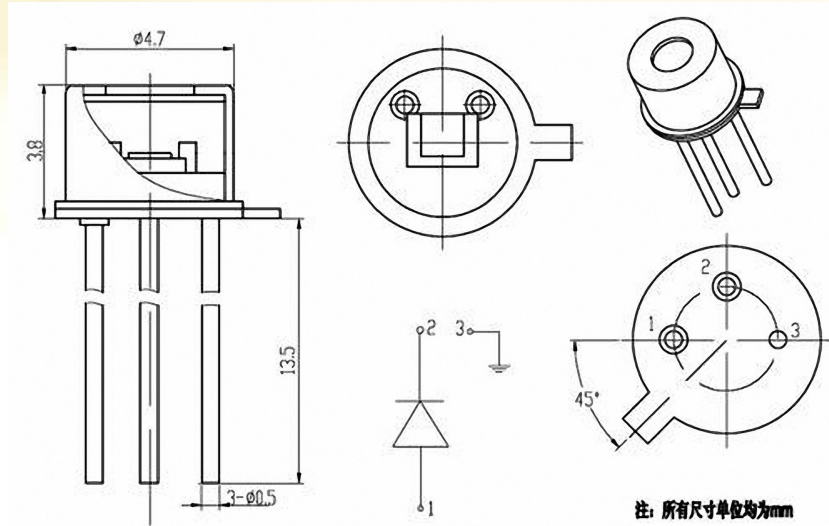
Operation Voltage	0 ~ -10		V
Linear Degree	± 0.15	± 0.15	dB
Plug Deviation	± 0.1	± 0.1	dB
Plug Lifespan	10 ⁵	10 ⁵	times
Max unsaturation efficiency	> 3	> 3	dBm
Forward Current	10		mA
Optical Current	10		mA
Backward Current	25		V
Power Consumption	100		mW
Operation Temperature	15 ~ 60		°C
Storage Temperature	-10 ~ 60		°C
Welding Condition	260 (10sec)		°C

Package



TO9 Package





TO46 Package

Notice

- 1、 All above curves is tested from some certain item, only for reference, the confirmed data are decided by confirmed detector.
- 2、 For more information, please contact Hi-Tech Optoelectronics Co., Ltd (HTOE)

